

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS[®]



Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

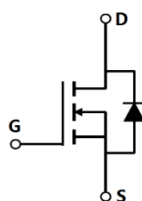
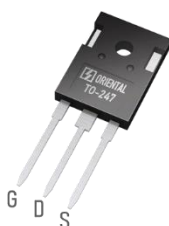
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, \min} @ T_{j(max)}$	600	V
I_D, pulse	69	A
$R_{DS(ON)}, \max @ V_{GS}=10V$	140	m Ω
Q_g	24.1	nC

Marking Information

Product Name	Package	Marking
OSG55R140HF	TO247	OSG55R140H

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	550	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	23	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		14.5	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	69	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	23	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	69	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	151	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	330	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0 \dots 480 \text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0 \dots 480 \text{ V}$, $I_{SD} \leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.82	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	550			V	$V_{GS}=0 \text{ V}$, $I_D=250 \mu\text{A}$
		600	670			$V_{GS}=0 \text{ V}$, $I_D=250 \mu\text{A}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2		4	V	$V_{DS}=V_{GS}$, $I_D=250 \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.11	0.14	Ω	$V_{GS}=10 \text{ V}$, $I_D=11.5 \text{ A}$
			0.34			$V_{GS}=10 \text{ V}$, $I_D=11.5 \text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30 \text{ V}$
				-100		$V_{GS}=-30 \text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=550 \text{ V}$, $V_{GS}=0 \text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1408.8		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		151.2		pF	
Reverse transfer capacitance	C_{rss}		4.14		pF	
Turn-on delay time	$t_{d(on)}$		40.5		ns	$V_{GS}=10\text{ V}$, $V_{DS}=420\text{ V}$, $R_G=25\ \Omega$, $I_D=23\text{ A}$
Rise time	t_r		73.5		ns	
Turn-off delay time	$t_{d(off)}$		63.6		ns	
Fall time	t_f		73.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		24.1		nC	$V_{GS}=10\text{ V}$, $V_{DS}=420\text{ V}$, $I_D=23\text{ A}$
Gate-source charge	Q_{gs}		9		nC	
Gate-drain charge	Q_{gd}		7.4		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=23\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		372		ns	$V_R=400\text{ V}$, $I_S=23\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		5.1		μC	
Peak reverse recovery current	I_{rrm}		25.6		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

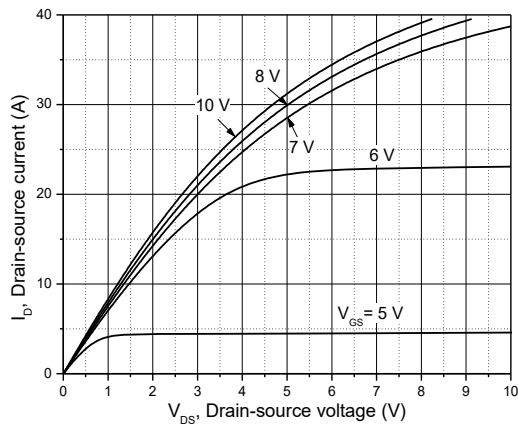


Figure 1. Typ. output characteristics

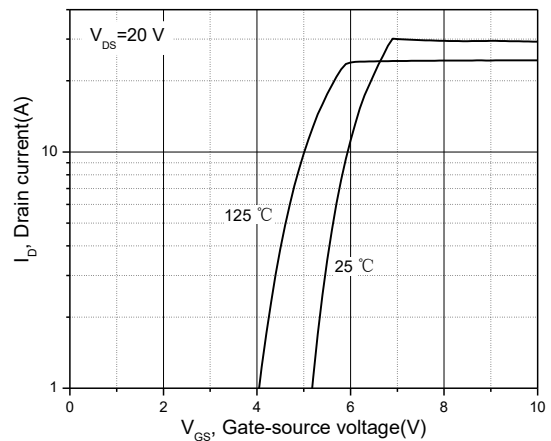


Figure 2. Typ. transfer characteristics

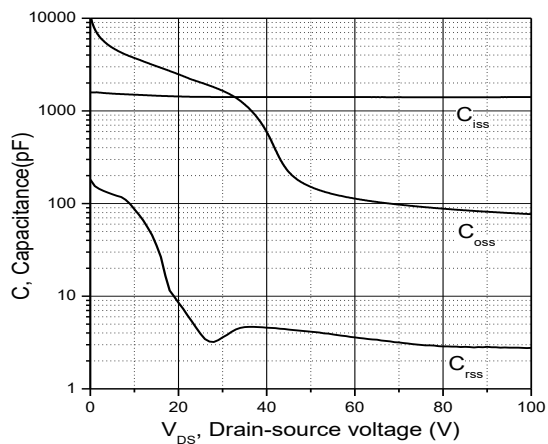


Figure 3. Typ. capacitances

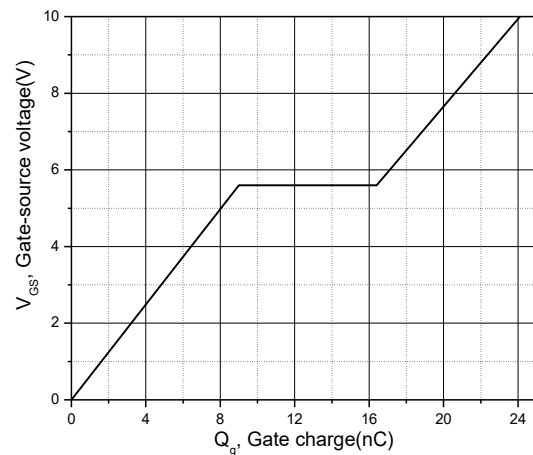


Figure 4. Typ. gate charge

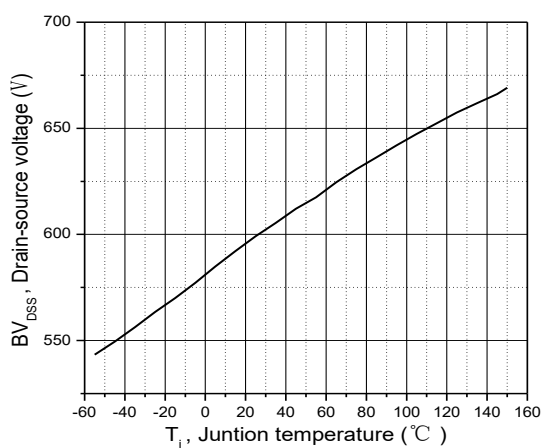


Figure 5. Drain-source breakdown voltage

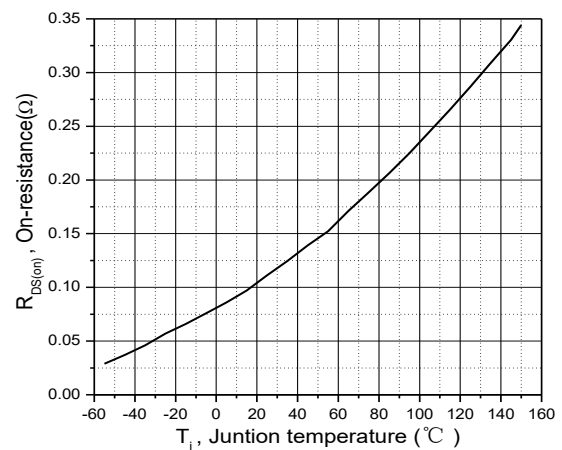


Figure 6. Drain-source on-state resistance

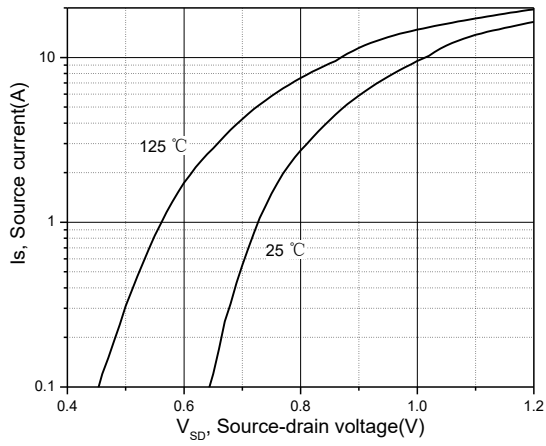


Figure 7. Forward characteristic of body diode

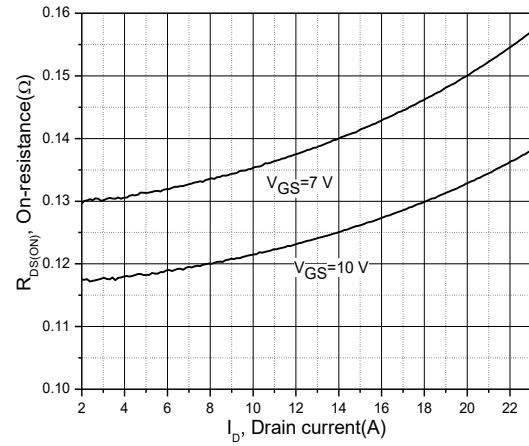


Figure 8. Drain-source on-state resistance

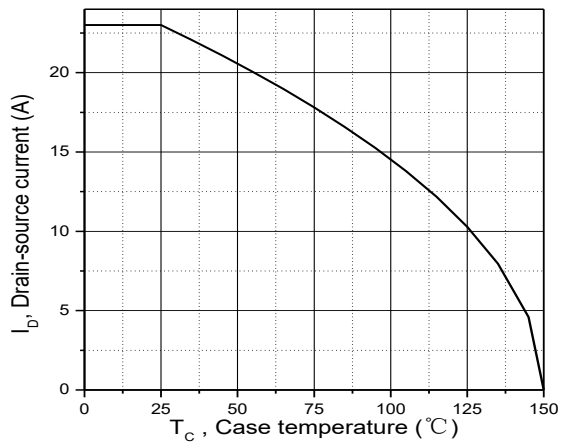


Figure 9. Drain current

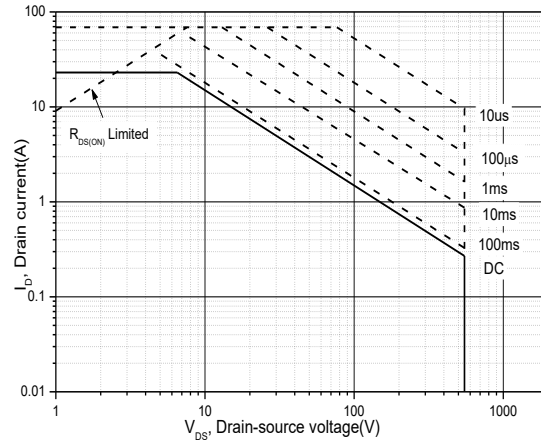


Figure 10. Safe operation area $T_C = 25\text{ }^{\circ}\text{C}$

Test circuits and waveforms

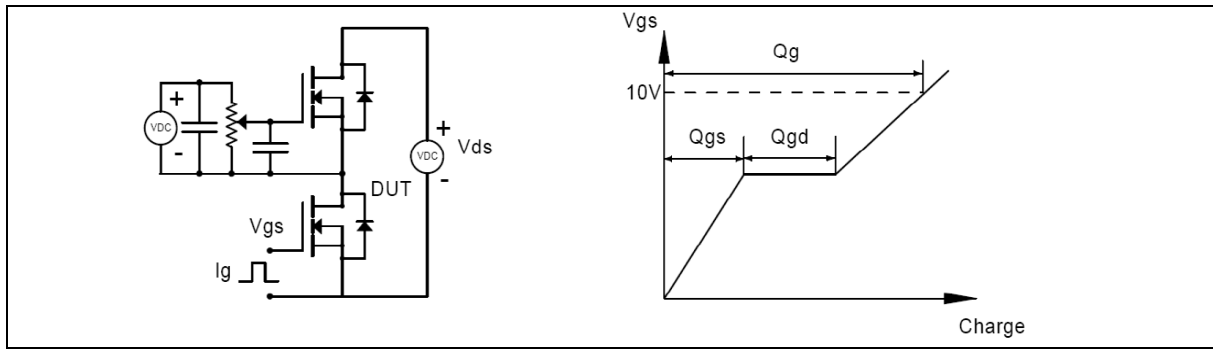


Figure 1. Gate charge test circuit & waveform

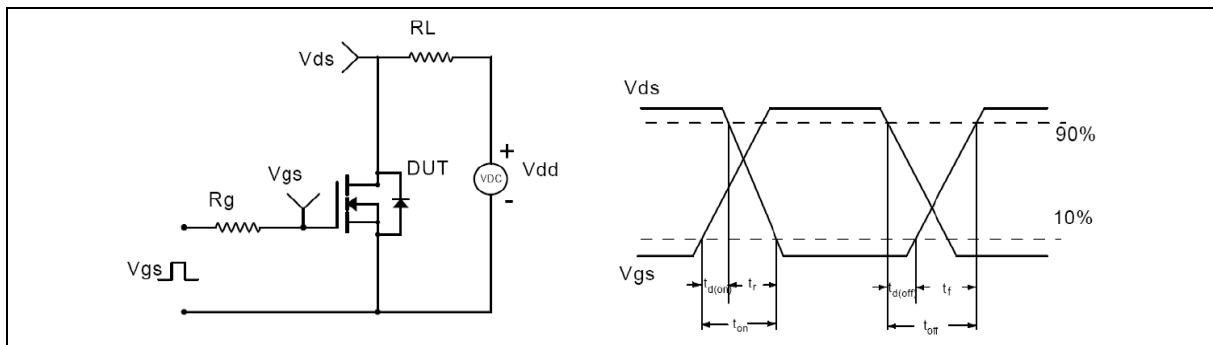


Figure 2. Switching time test circuit & waveforms

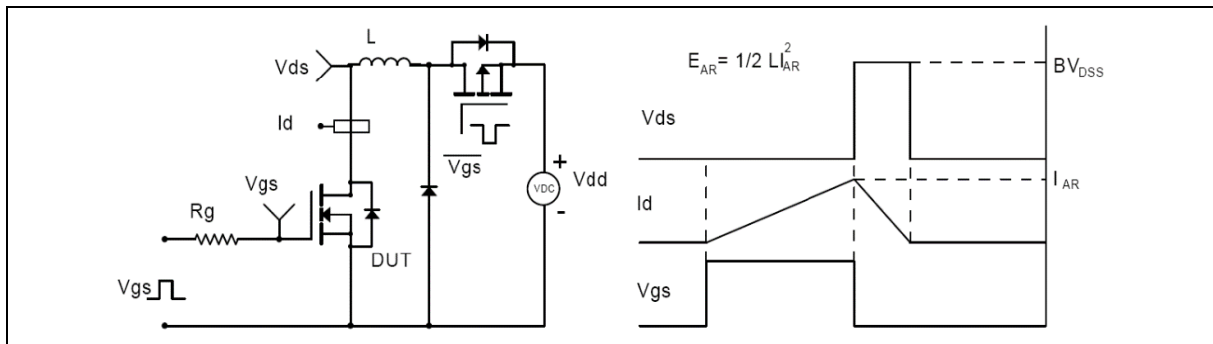


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

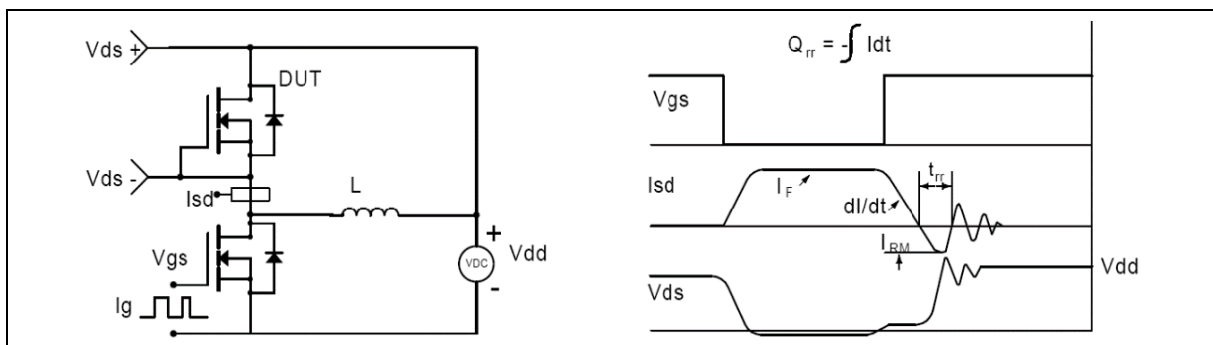
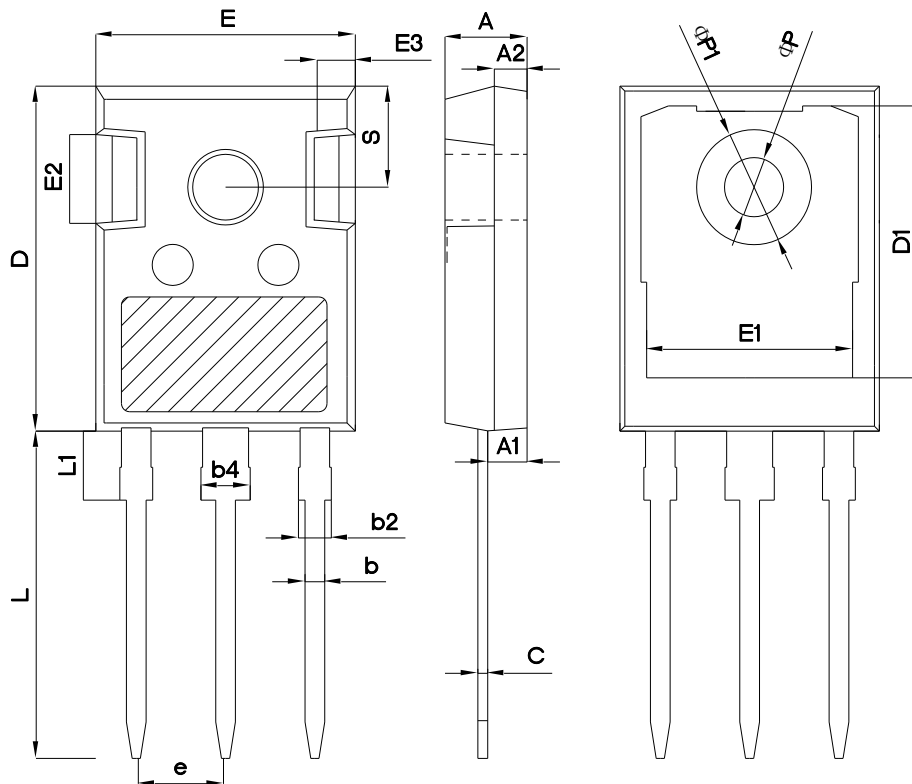


Figure 4. Diode reverse recovery test circuit & waveforms

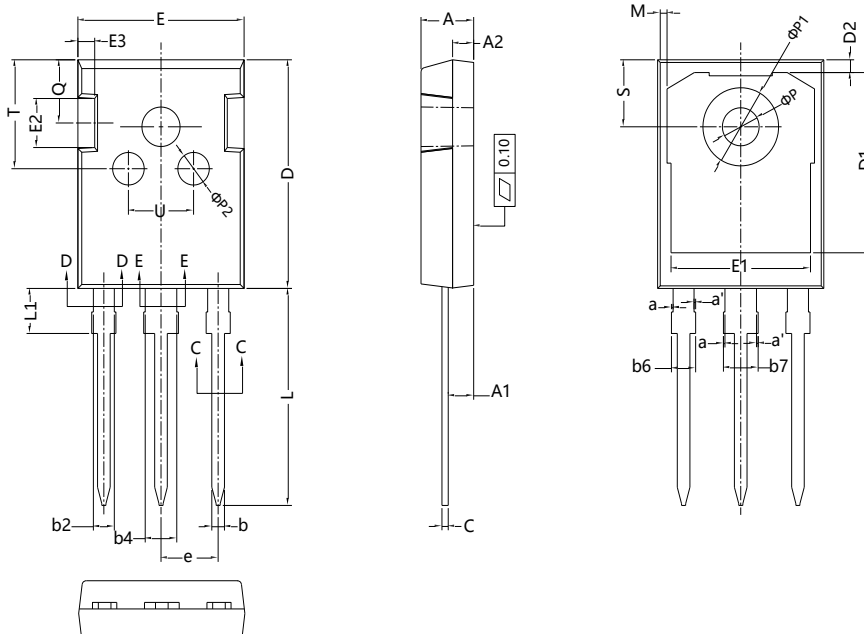
Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15 BSC		

Version 1: TO247-P package outline dimension

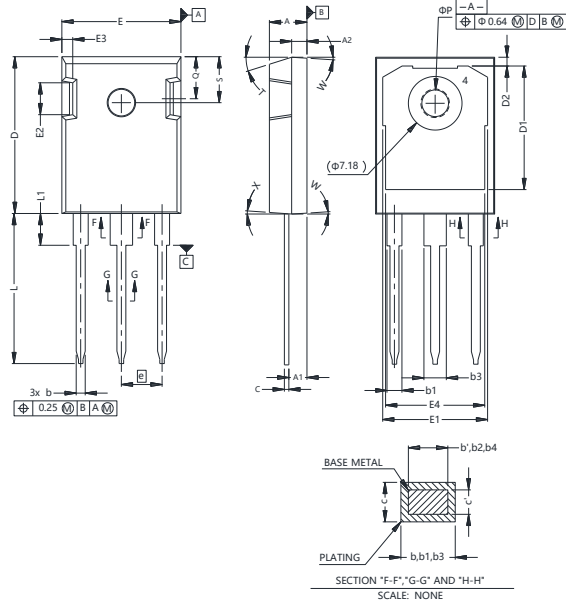
Package Information



Symbol	mm		
	Min	Nom	Max
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0.00	-	0.15
a'	0.00	-	0.15
b	1.16	-	1.26
b2	1.96	-	2.06
b4	2.96	-	3.06
b6	-	-	2.25
b7	-	-	3.25
c	0.59	-	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.40	4.50	4.60
E3	1.50	1.60	1.70
e	5.436 BSC		
L	19.80	19.92	20.10
L1	-	-	4.30
M	0.35	-	0.95
P	3.40	3.50	3.60
P1	7.00	-	7.40
P2	2.40	2.5	2.6
Q	5.60	-	6.0
S	6.05	6.15	6.25
T	9.8	-	10.20
U	6.00	-	6.40

Version 2: TO247-J package outline dimension

Package Information



Symbol	mm	
	Min	Max
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b'	1.07	1.28
b	1.07	1.33
b1	1.91	2.41
b2	1.91	2.16
b3	2.87	3.38
b4	2.87	3.13
c'	0.55	0.65
c	0.55	0.68
D	20.80	21.10
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	5.44 BSC	
N	3	
L	19.81	20.32
L1	4.10	4.40
øP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF	
W	3.5° REF	
X	4° REF	

Version 3: TO247-S package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-P	30	11	330	6	1980
TO247-J	30	20	600	4	2400
TO247-S	30	15	450	4	1800

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG55R140HF	TO247	yes	yes	yes

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